

MSB92ASWT1 Datasheet



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DiGi Electronics Part Number MSB92ASWT1-DG

Manufacturer onsemi

Manufacturer Product Number MSB92ASWT1

Description TRANS PNP 300V 0.5A SC70-3

Detailed Description Bipolar (BJT) Transistor PNP 300 V 500 mA 50MHz 1

50 mW Surface Mount SC-70-3 (SOT323)



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
MSB92ASWT1	onsemi
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
PNP	500 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
300 V	500mV @ 2mA, 20mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
250nA (ICBO)	120 @ 1mA, 10V
Power - Max:	Frequency - Transition:
150 mW	50MHz
Operating Temperature:	Mounting Type:
150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
SC-70, SOT-323	SC-70-3 (SOT323)
Base Product Number:	
MSB92	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
RoHS non-compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0095	

Onsemi

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PNP Silicon General Purpose High Voltage Transistor

MSB92ASWT1G, MSB92AS1WT1G

This PNP Silicon Planar Transistor is designed for general purpose amplifier applications. This device is housed in the SC-70/SOT-323 package which is designed for low power surface mount applications.

Features

 These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

Symbol	Rating	Value	Unit
V _{(BR)CBO}	Collector-Base Voltage	-300	Vdc
V _{(BR)CEO}	Collector-Emitter Voltage	-300	Vdc
V _{(BR)EBO}	Emitter-Base Voltage	-5.0	Vdc
I _C	Collector Current - Continuous	500	mAdc
ESD	ESD Rating: Human Body Model Machine Model	Class 1C Class C	-

THERMAL CHARACTERISTICS

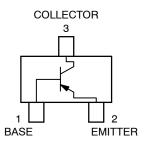
Symbol	Rating	Max	Unit
P _D	Power Dissipation (Note 1)	150	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

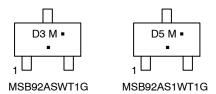
 Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.



SC-70 (SOT-323) CASE 419 STYLE 3



MARKING DIAGRAM



Dx = Device Code
M = Date Code*
• = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	•	Package	Shipping [†]
MSB92AS	WT1G	SC-70 (Pb-Free)	3,000/Tape & Reel

DISCONTINUED (Note 1)

1

MSB92AS1WT1G	SC-70	3,000/Tape & Reel
	(Pb-Free)	

- †For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.
- DISCONTINUED: This device is not recommended for new design. Please contact your onsemi representative for information. The most current information on this device may be available on www.onsemi.com.

MSB92ASWT1G, MSB92AS1WT1G

ELECTRICAL CHARACTERISTICS

Symbol	Characteristic	Min	Max	Unit
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage $(I_C = -1.0 \text{ mAdc}, I_B = 0)$	-300	-	Vdc
V _{(BR)CBO}	Collector-Base Breakdown Voltage ($I_C = -100 \mu Adc$, $I_E = 0$)	-300	ı	Vdc
V _{(BR)EBO}	Emitter-Base Breakdown Voltage ($I_E = -100 \mu Adc$, $I_E = 0$)	-5.0	-	Vdc
І _{СВО}	Collector-Base Cutoff Current $(V_{CB} = 300 \text{ Vdc}, I_E = 0)$	-	-0.25	μΑ
I _{EBO}	Emitter-Base Cutoff Current (V _{EB} = -3.0 Vdc, I _B = 0)	-	-0.1	μΑ
h _{FE1} h _{FE2} h _{FE3}	DC Current Gain (Note 2)	120 40 25	200 - -	-
V _{CE(sat)}	Collector-Emitter Saturation Voltage (Note 2) $(I_C = -20 \text{ mAdc}, I_B = -2.0 \text{ mAdc})$		-0.5	Vdc
V _{BE(sat)}	Base–Emitter Saturation Voltage ($I_C = -20$ mAdc, $I_B = -2.0$ mAdc)	_	-0.9	Vdc

SMALL SIGNAL CHARACTERISTICS

f _T	Current – Gain – Bandwidth Product ($I_C = -10 \text{ mAdc}$, $V_{CE} = -20 \text{ Vdc}$, $f = 20 \text{ MHz}$)	50	-	MHz
C _{cb}	Collector-Base Capacitance (V _{CB} = -20 Vdc, I _E = 0, f = 1.0 MHz)	-	6.0	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width \leq 300 µs, D.C. \leq 2%.

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TYPICAL CHARACTERISTICS

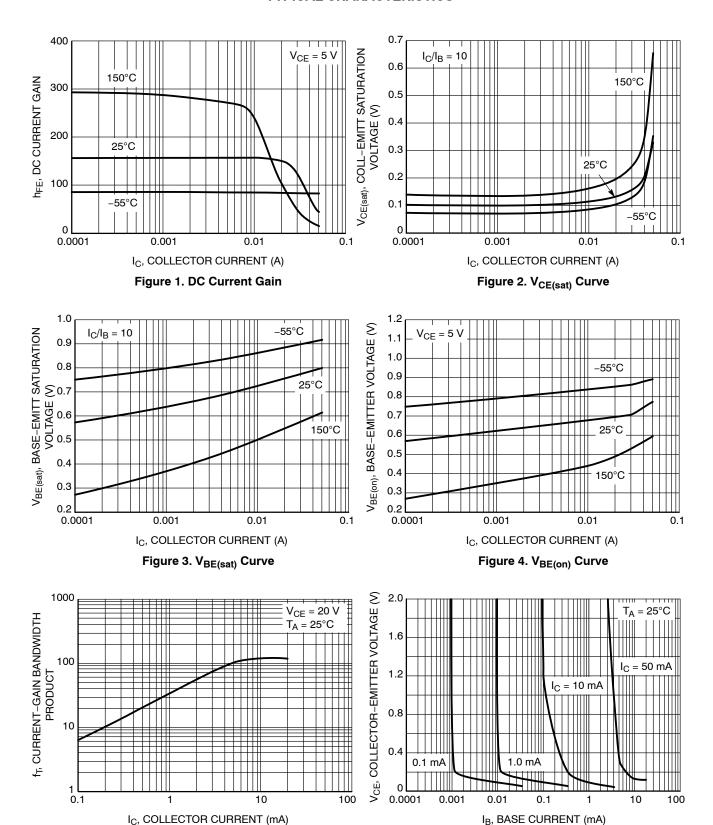
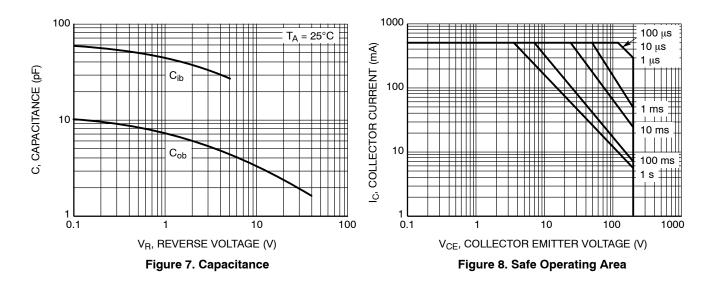


Figure 5. Current-Gain Bandwidth Product

Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS (continued)





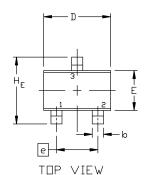
MECHANICAL CASE OUTLINE

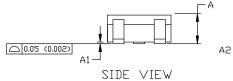
PACKAGE DIMENSIONS

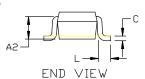


DATE 11 OCT 2022









NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 BS	C
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BS	C
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



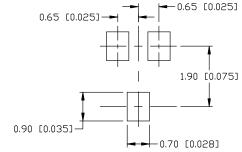


XX = Specific Device Code

= Date Code М

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	CATHODE
COLLECTOR	COLLECTOR	3. DRAIN	CATHODE-ANODE	3. ANODE-CATHODE	CATHODE

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DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1	

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